# Quad 2-Channel Multiplexer with 3-State Outputs

The MC74LVX257 is an advanced high speed CMOS quad 2-channel multiplexer fabricated with silicon gate CMOS technology. It consists of four 2-input digital multiplexers with common select (S) and enable  $(\overline{OE})$  inputs. When  $(\overline{OE})$  is held High, selection of data is inhibited and all the outputs go Low.

The select decoding determines whether the A or B inputs get routed to the corresponding Y outputs.

The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

#### **Features**

- High Speed:  $t_{PD} = 4.5 \text{ ns}$  (Typ) at  $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A \text{ (Max)}$  at  $T_A = 25 \text{°C}$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- Chip Complexity: FETs = 100; Equivalent Gates = 25
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

• Pb-Free Packages are Available\*

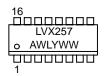


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MARKING DIAGRAMS



SOIC-16 D SUFFIX CASE 751B



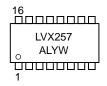


TSSOP-16 DT SUFFIX CASE 948F





SOEIAJ-16 M SUFFIX CASE 966



A = Assembly Location

WL or L = Wafer Lot Y = Year WW or W = Work Week

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

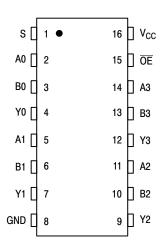


Figure 1. Pin Assignment

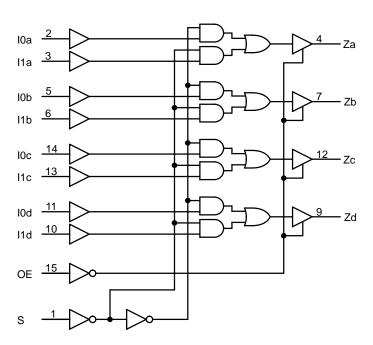


Figure 2. Expanded Logic Diagram

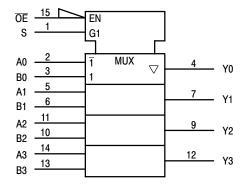


Figure 3. IEC Logic Symbol

#### **FUNCTION TABLE**

Inp	outs	Outputs
ŌĒ	S	Y0 – Y3
Н	Х	Z
L	L	A0-A3
L	Н	B0-B3

A0 - A3, B0 - B3 =the levels of the respective Data-Word Inputs.

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LVX257D	SOIC-16	48 Units / Rail
MC74LVX257DG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74LVX257DR2	SOIC-16	2500 Tape & Reel
MC74LVX257DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74LVX257DT	TSSOP-16*	96 Units / Rail
MC74LVX257DTR2	TSSOP-16*	2500 Tape & Reel
MC74LVX257M	SOEIAJ-16	50 Units / Rail
MC74LVX257MEL	SOEIAJ-16	2000 Tape & Reel
MC74LVX257MELG	SOEIAJ-16 (Pb-Free)	2000 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*This package is inherently Pb–Free.

#### **MAXIMUM RATINGS**

Symbol	Para	ameter	Value	Unit
V <sub>CC</sub>	Positive DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	Digital Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage		-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Diode Current		-20	mA
I <sub>OK</sub>	Output Diode Current		±20	mA
I <sub>OUT</sub>	DC Output Current, per Pin		±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins		±75	mA
P <sub>D</sub>	Power Dissipation in Still Air	SOIC Package TSSOP	200 180	mW
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2) Charged Device Model (Note 3)	>2000 >200 >2000	V
I <sub>LATCHU</sub> P	Latchup Performance	Above V <sub>CC</sub> and Below GND at 125°C (Note 4)	±300	mA
$\theta_{JA}$	Thermal Resistance, Junction-to-Ambient	SOIC Package TSSOP	143 164	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. Tested to EIA/JESD22-A114-A
- 2. Tested to EIA/JESD22-A115-A
- 3. Tested to JESD22-C101-A
- 4. Tested to EIA/JESD78

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Characteristics	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	3.6	V
V <sub>IN</sub>	DC Input Voltage	0	5.5	V
V <sub>OUT</sub>	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, all Package Types	-40	85	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise or Fall Time $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0	100	ns/V

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

# DC CHARACTERISTICS (Voltages Referenced to GND)

			V <sub>CC</sub>	T <sub>A</sub> = 25°C		$-40^{\circ}\text{C} \leq \text{T}_{\text{A}} \leq 85^{\circ}\text{C}$			
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 3.6	0.75 V <sub>CC</sub> 0.7 V <sub>CC</sub> 0.7 V <sub>CC</sub>			0.75 V <sub>CC</sub> 0.7 V <sub>CC</sub> 0.7 V <sub>CC</sub>		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 3.6			0.25 V <sub>CC</sub> 0.3 V <sub>CC</sub> 0.3 V <sub>CC</sub>		0.25 V <sub>CC</sub> 0.3 V <sub>CC</sub> 0.3 V <sub>CC</sub>	V
V <sub>OH</sub>	High-Level Output Voltage	$I_{OH} = -50 \mu A$ $I_{OH} = -50 \mu A$ $I_{OH} = -4 \text{ mA}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V <sub>OL</sub>	Low-Level Output Voltage	$I_{OL} = 50 \mu A$ $I_{OL} = 50 \mu A$ $I_{OL} = 4 \text{ mA}$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
I <sub>OZ</sub>	Maximum 3–State Leakage Current	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	3.6			±0.1		±1.0	μΑ
I <sub>IN</sub>	Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 3.6			±0.1		±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per package)	$V_{IN} = V_{CC}$ or GND	3.6	1.0	1.0	2.0		40	μΑ

# AC ELECTRICAL CHARACTERISTICS Input $t_r = t_f = 3.0 \text{ ns}$

					T <sub>A</sub> = 25°C	;	-40°C ≤	T <sub>A</sub> ≤ 85°C	
Symbol	Parameter	Test Conditi	ons	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A or B to Y	V <sub>CC</sub> = 2.7 V	$C_L = 15pF$ $C_L = 50pF$		6.5 9.5	10.0 14.0	1.0 1.0	15.0 18.5	ns
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		4.5 7.5	8.0 12.0	1.0 1.0	10.0 13.5	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, S to Y	V <sub>CC</sub> = 2.7 V	$C_L = 15pF$ $C_L = 50pF$		8.0 10.5	12.0 15.5	1.0 1.0	17.0 20.0	ns
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		6.0 8.5	10.0 13.5	1.0 1.0	12.0 15.5	
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Output Enable, Time, OE to Y	$V_{CC} = 2.7 \text{ V}$ $R_L = 1 \text{ k}\Omega$	$C_L = 15pF$ $C_L = 50pF$		7.5 10.5	11.5 15.0	1.0 1.0	16.5 18.0	ns
		$V_{CC}$ = 3.3 V ± 0.3 V $R_L$ = 1 k $\Omega$	$C_L = 15pF$ $C_L = 50pF$		5.5 8.5	9.5 13.0	1.0 1.0	11.5 15.0	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Output Disable, Time, OE to Y	$V_{CC} = 2.7$ $R_L = 1 \text{ k}\Omega$	C <sub>L</sub> = 50pF		13.0	17.0	1.0	18.0	ns
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C <sub>L</sub> = 50pF		12	17.0	1.0	18.0	
C <sub>IN</sub>	Maximum Input Capacitance				4	10		10	pF
		•			Typica	@ 25°C, \	/ <sub>CC</sub> = 3.3 V		
$C_{PD}$	Power Dissipation Capacitance (Note 5)			20			pF		

<sup>5.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \cdot C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .

# **NOISE CHARACTERISTICS** Input $t_{\text{r}}$ = $t_{\text{f}}$ = 3.0 ns, $C_{\text{L}}$ = 50 pF, $V_{\text{CC}}$ = 3.3 V

		T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.5	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.3	-0.5	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

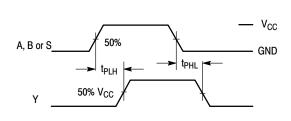


Figure 4. Switching Waveform

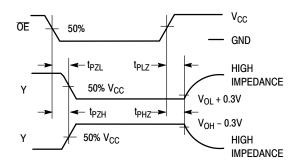
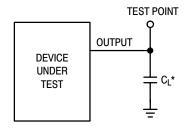


Figure 5. Switching Waveform



\*Includes all probe and jig capacitance

\*Includes all probe and jig capacitance

Figure 6. Test Circuit

Figure 7. Test Circuit

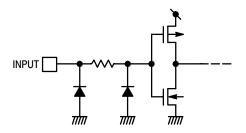
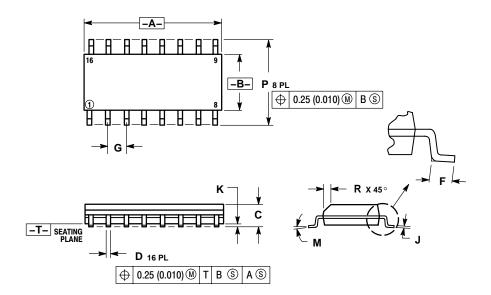


Figure 8. Input Equivalent Circuit

#### PACKAGE DIMENSIONS

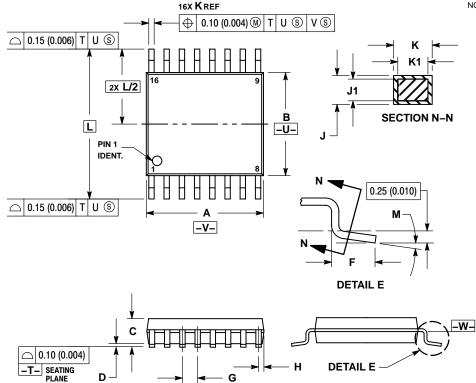
#### SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

#### TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE A**



#### NOTES:

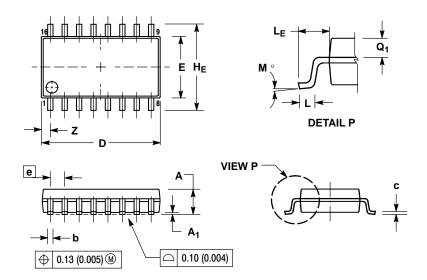
- JIES:

  1. DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD
  FLASH. PROTRUSIONS OR GATE BURRS.
  MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL
  NOT EXCEED 0.25 (0.010) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE
  DAMBAR PROTRUSION. ALLOWABLE
- DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE—W...

	MILLIN	IETERS		HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
М	0°	8°	0°	8 °

#### SOEIAJ-16 **M SUFFIX** CASE 966-01 ISSUE O



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
  PER SIDE.

  4. TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT
  INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
  TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION.
  DAMBAR CANNOT BE LOCATED ON THE LOWER
  RADIUS OR THE FOOT MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD
  TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		0.78		0.031

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